SGS-THOMSON MICROELECTRONICS

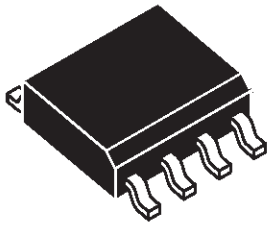
TPN3021

Application Specific Discretes
A.S.D.™

TRIPOLAR OVERVOLTAGE PROTECTION FOR NETWORK INTERFACES

FEATURES

- TRIPLE CROWBAR PROTECTION
- PEAK PULSE CURRENT : I_{PP} = 30 A, 10/1000 µs
- VERY LOW CAPACITANCE : C = 30 pF
- PROTECTS HIGH-SPEED LINE DRIVERS / RECEIVERS



SO8

DESCRIPTION

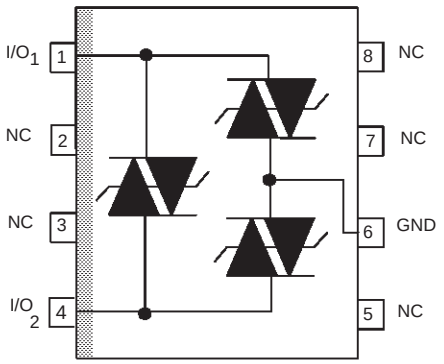
Dedicated to dataline protection, this device provides a triple protection function. It ensures the same protection capability with the same breakdown voltage both in common mode and in differential mode.

With a stand-off voltage of 28V and a very low capacitance, this device is able to protect high-speed interfaces such as T1/E1 interface.

COMPLIES WITH THE FOLLOWING STANDARDS :

- IEC801-2	15kV	(air discharge)
- IEC801-4	40A	(repetitive 2.5kHz)
- IEC801-5	1.2/50µs	4kV
	8/20µs	100A

SCHEMATIC DIAGRAM



ABSOLUTE MAXIMUM RATINGS (T_{amb} = 25 °C)

Symbol	Parameter		Value	Unit
I_{pp}	Peak pulse current	10/1000 µs 8/20 µs	30 150	A A
T_{stg} Tj	Storage temperature range Maximum junction temperature		- 40 to + 150 150	°C °C
T_L	Maximum lead temperature for soldering during 10s		260	°C

THERMAL RESISTANCE

Symbol	Parameter	Value	Unit
$R_{th(j-a)}$	Junction to ambient	170	°C/W

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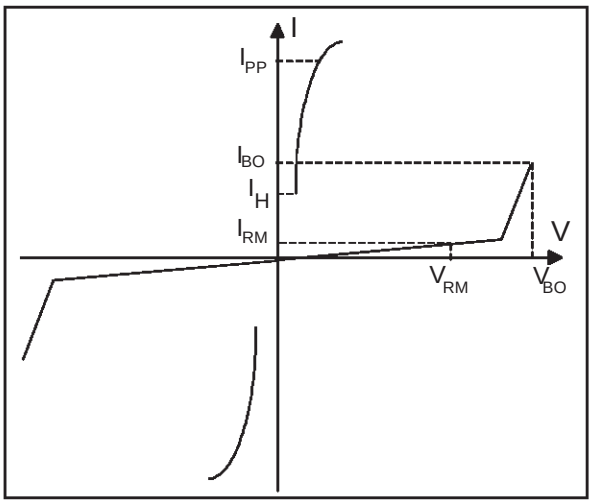
ELECTRICAL CHARACTERISTICS (T_{amb}=25°C)

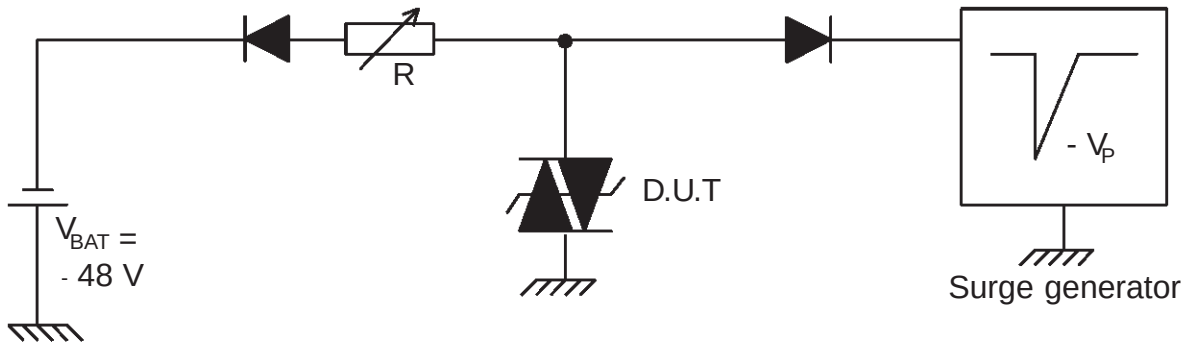
Symbol	Parameter
V_{RM}	Stand-off voltage
V_{BO}	Breakover voltage
V_{BR}	Breakdown voltage
I_H	Holding current
I_{BO}	Breakover current
I_{RM}	Leakage current at V_{RM}
I_{PP}	Peak pulse current
C	Capacitance
αT	Temperature coefficient



Type	I_{RM} @ V_{RM} max. note 1		V_{BO} @ I_{BO} max.		I_H min. note 2	C typ. note 3	C max. note 3	αT typ. note 4
	µA	V	V	mA	mA	pF	pF	10^{-4}/°C
TPN3021	4	28	38	100	30	25	30	8

Note 1 : Between any I/O pin and Ground or between I/O_1 and I/O_2.
Note 2 : See the functional holding current (I_H) test circuit.
Note 3 : Between any I/O pin and GND or between I/O_1 and I/O_2 at 0V bias, V_{RMS} = 30 mV, F = 1 MHz.
Note 4 : $\Delta V_{BO} = \alpha T \times (T_{amb} - 25) \times V_{BO}(25°C)$.

FUNCTIONAL HOLDING CURRENT (I_H) TEST CIRCUIT : GO-NO GO TEST



This is a GO-NO GO test which allows to confirm the holding current (I_H) level in a functional test circuit.

TEST PROCEDURE :

- Adjust the current level at the I_H value by short circuiting the D.U.T.
- Fire the D.U.T. with a surge current : I_{pp} = 10A, 10/1000 µs.
- The D.U.T. will come back to the off-state within a duration of 50 ms max.

APPLICATION CIRCUIT : T1/E1 Interface Protection

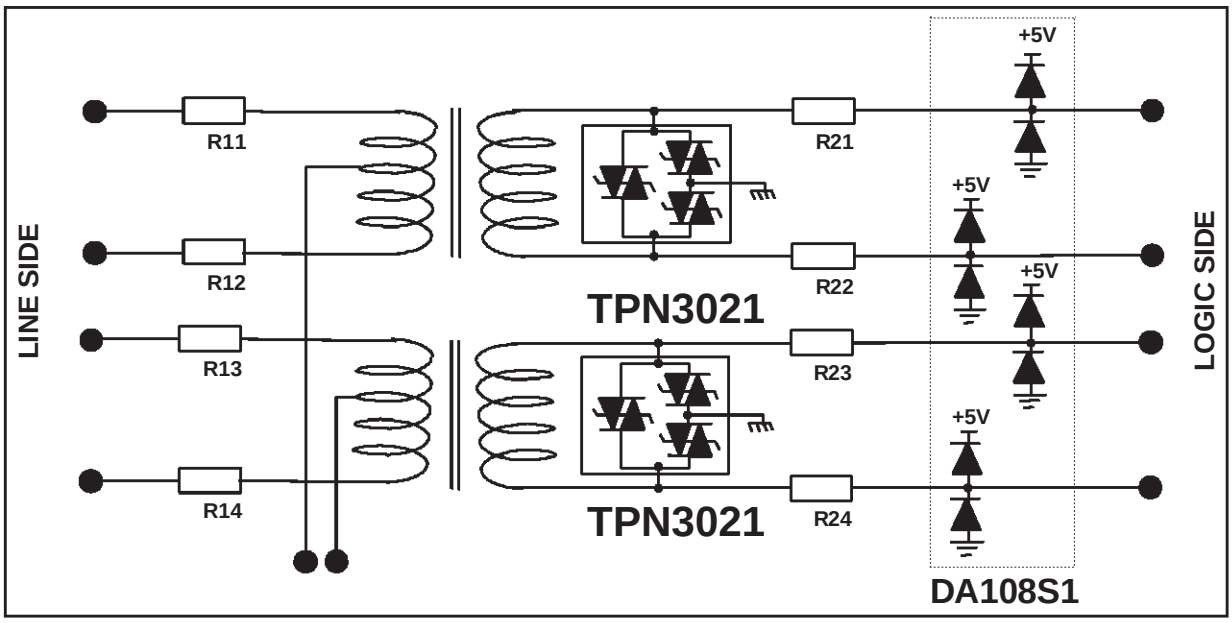
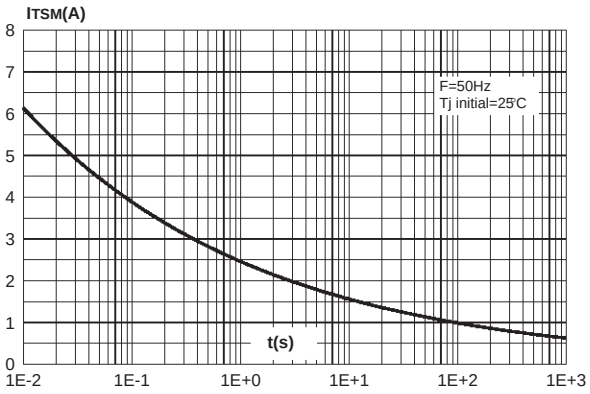
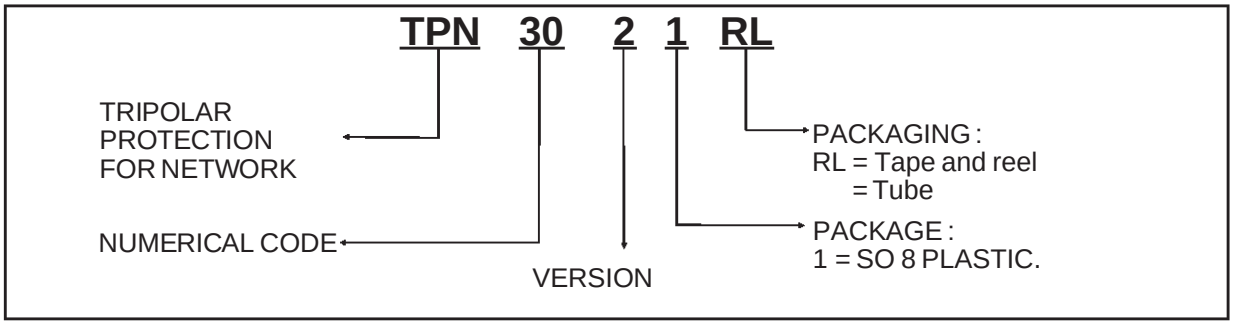


Fig. 1 : Surge peak current versus overload duration.



ORDER CODE

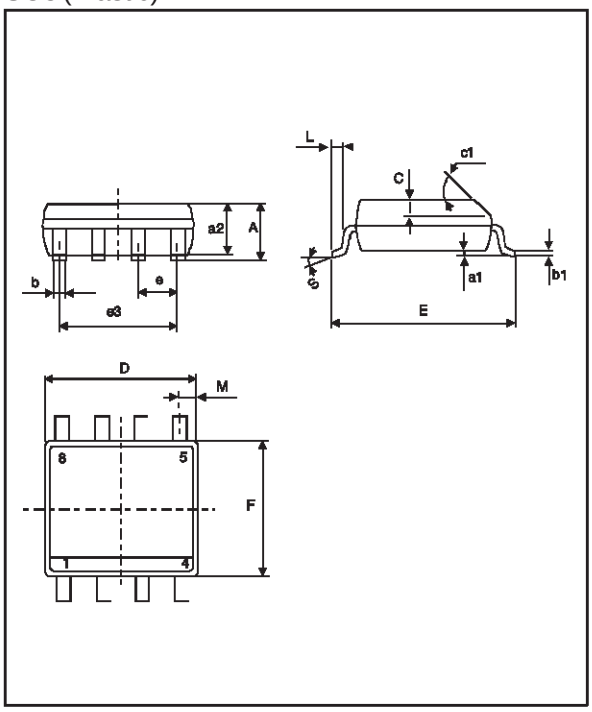


Marking

Type	Marking
TPN3021	TPN302

PACKAGE MECHANICAL DATA

SO8 (Plastic)



REF.	DIMENSIONS					
	Millimetres			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A			1.75			0.069
a1	0.1		0.25	0.004		0.010
a2			1.65			0.065
b	0.35		0.48	0.014		0.019
b1	0.19		0.25	0.007		0.010
C		0.50			0.020	
c1	45° (typ)					
D	4.8		5.0	0.189		0.197
E	5.8		6.2	0.228		0.244
e		1.27			0.050	
e3		3.81			0.150	
F	3.8		4.0	0.15		0.157
L	0.4		1.27	0.016		0.050
M			0.6			0.024
S	8° (max)					

Packaging = Products supplied in antistatic tubes or tape and reel.

Weight = 0.08 g